

This listing of claims will replace all prior versions of claims in the application.

Claims 1-77. (cancelled)

78. (new) A chemically-amplified positive photoresist composition comprising 1) a resin that comprises phenolic and alkyl acrylate groups, 2) a photoacid generator compound, and 3) lactic acid or acetic acid.

79. (new) The photoresist of claim 78 wherein the lactic acid or acetic acid is present in an amount of at least about 1 weight percent based on total solids of the photoresist composition.

80. (new) The photoresist of claim 78 further comprising a basic component.

81. (new) The photoresist of claim 80 wherein the basic component is an amine.

82. (new) The photoresist of claim 78 wherein the photoresist comprises a solvent that contains an ester moiety.

83. (new) The photoresist of claim 82 wherein the photoresist comprises a solvent component that comprises ethyl lactate.

84. (new) The photoresist of claim 83 wherein the acid is lactic acid.

85. (new) The photoresist of claim 78 wherein the photoresist comprises a solvent component that comprises propylene glycol methyl ether acetate.

86. (new) The photoresist of claim 85 wherein the acid is acetic acid.
87. (new) A chemically-amplified positive photoresist composition comprising:
- 1) i) a resin that comprises polymerized units of cyclic olefin groups and/or anhydride groups, or ii) a fluoro-substituted resin,
  - 2) a photoacid generator compound, and
  - 3) lactic acid or acetic acid.
88. (new) The photoresist of claim 87 wherein the lactic acid or acetic acid is present in an amount of at least about 1 weight percent based on total solids of the photoresist composition.
89. (new) The photoresist of claim 87 further comprising a basic component.
90. (new) The photoresist of claim 89 wherein the basic component is an amine.
91. (new) The photoresist of claim 87 wherein the photoresist comprises a resin that comprises polymerized units of cyclic olefin groups and/or anhydride groups.
92. (new) The photoresist of claim 87 wherein the photoresist comprises a fluoro-substituted resin.
93. (new) The photoresist of claim 87 wherein the photoresist comprises a solvent that contains an ester moiety.
94. (new) The photoresist of claim 93 wherein the photoresist comprises a solvent component that comprises ethyl lactate.

95. (new) The photoresist of claim 94 wherein the acid is lactic acid.
96. (new) The photoresist of claim 87 wherein the photoresist comprises a solvent component that comprises propylene glycol methyl ether acetate.
97. (new) The photoresist of claim 96 wherein the acid is acetic acid.
98. (new) A chemically-amplified positive photoresist composition comprising 1) a resin that is at least essentially free of aromatic groups, 2) a photoacid generator compound, and 3) lactic acid or acetic acid.
99. (new) The photoresist of claim 98 wherein the lactic acid or acetic acid is present in an amount of at least about 1 weight percent based on total solids of the photoresist composition.
100. (new) The photoresist of claim 98 further comprising a basic component.
101. (new) The photoresist of claim 100 wherein the basic component is an amine.
102. (new) The photoresist of claim 98 wherein the photoresist comprises a solvent that contains an ester moiety.
103. (new) The photoresist of claim 102 wherein the photoresist comprises a solvent component that comprises ethyl lactate.
104. (new) The photoresist of claim 103 wherein the acid is lactic acid.

105. (new) The photoresist of claim 98 wherein the photoresist comprises a solvent component that comprises propylene glycol methyl ether acetate.

106. (new) The photoresist of claim 105 wherein the acid is acetic acid.

107. (new) The photoresist of claim 98 wherein the resin comprises polymerized units of cyclic olefin groups and/or anhydride groups.

108. (new) The photoresist of claim 98 wherein the resin comprises a fluoro-substituted resin.

109. (new) A chemically-amplified positive photoresist composition comprising 1) a resin that comprises phenolic and alkyl acrylate groups, 2) a photoacid generator compound, 3) lactic acid or acetic acid, and 4) a basic component.

110. (new) The photoresist of claim 109 wherein the lactic acid is present in an amount of at least about 0.5 weight percent based on total solids of the photoresist composition.

111. (new) The photoresist of claim 109 wherein the lactic acid is present in an amount of at least about 1 weight percent based on total solids of the photoresist composition.

112. (new) The photoresist of claim 109 wherein the basic component is an amine.

113. (new) A method of producing an article of manufacture comprising:  
(a) applying a coating layer of a photoresist of claim 78 on a wafer substrate; and  
(b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a photoresist relief image.

114. (new) A method of producing an article of manufacture comprising:  
(a) applying a coating layer of a photoresist of claim 87 on a wafer substrate; and  
(b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a photoresist relief image.

115. (new) A method of producing an article of manufacture comprising:  
(a) applying a coating layer of a photoresist of claim 98 on a wafer substrate; and  
(b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a photoresist relief image.

116. (new) A method of producing an article of manufacture comprising:  
(a) applying a coating layer of a photoresist of claim 109 on a wafer substrate; and  
(b) exposing the photoresist coating layer to patterned activating radiation and developing the exposed photoresist layer to provide a photoresist relief image.